

Low power, Dual Operational Amplifier in bare die form

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Description

The LM358 consists of x2 independent, high gain, internally frequency compensated operational amplifiers operating from a single power supply as low as 3V or as high as 32V. The device is useful in interface circuits with digital systems and can be operated from the single common 5V power supply. The device also finds use in transducer amplifiers, DC gain blocks & many other conventional op-amp circuits which benefit from the single power supply capability. $I_{\rm Q}$ per amplifier is about 1/5 of the industry 741. Split-supply operation is also possible with supply current drain independent of voltage supplied for low power. The die size is one of the smallest in the industry.

Ordering Information

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For a higher electrical grade version of this product please see

LM358A

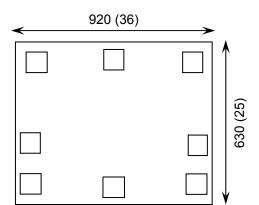
For High Reliability versions of this product please see

LM158 and (1) 456A

Features:

- Temperature compensated bandwidth (unity gain)
- Temperature compensated I_B: 45 nA
- Wide power supply range, single upply: 3V-32V or dual supplies: ±1.5V o ± 6V
- Low V_{os}: 2mV, and I_{os}: 5nA
- Differential input voltage range equal to the power supply voltage
- Large output voltage: 0V to V_{CC} -1.5V swing
- Input Compon-Mode Voltage range includes GND

Die Dipiensions in µm (mils)



Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(15 Mils) On request
- Assembled into Ceramic Package On request

Mechanical Specification

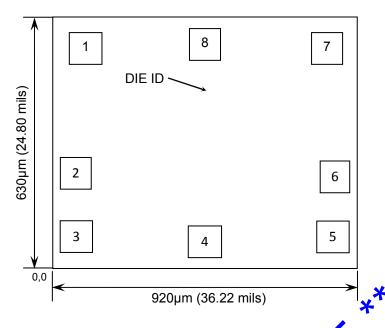
Die Size (Unsawn)	920 x 630 36 x 25	µm mils		
Minimum Bond Pad Size	85 x 85 3.35 x 3.35	μm mils		
Die Thickness	350 (±20) μr 13.78 (±0.79) mi			
Top Metal Composition	Al 1%Si 1.1μ	m		
Back Metal Composition	N/A – Bare Si			





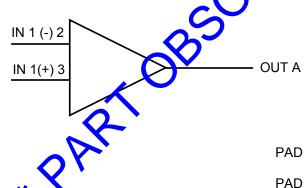
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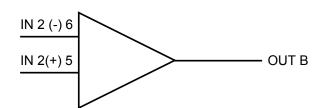
Pad Layout and Functions



PAD	FUNCTION	COORD	INATES				
		X	Υ				
1	OUTPUT A	0.1285	0.5015				
2	- INPUT A	0.1125	0.2425				
3	+ INCUT	0.1125	0.1125				
4	GND	0.4600	0.1075				
5	+INPUT B	0.8075	0.1125				
	– INPUT B	0.8075	0.2425				
	ОИТРИТ В	0.7915	0.5015				
8	V _{CC}	0.4600	0.5175				
CHIP BACK POTENTIAL IS FLOAT							

Logic Diagram





PAD 8 = V_{CC}

PAD 4 = GND



Absolute Maximum Ratings¹

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PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage – Single Supply	V _{cc}	32	V
Supply Voltage – Split Supply	• • • • • • • • • • • • • • • • • • • •	±16	X
Input Differential Voltage Range	V_{IDR}	32	
Input Common Mode Voltage Range	V_{ICR}	-0.3 to 32	V
Output Short Circuit to Ground	-	Continuous	-
Junction Temperature	T_J	150	°C
Input Current (per pin) ²	I _{IN}	50	mA

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute haximum ratings, for extended periods, may reduce device reliability.

Recommended Operating Conditions

PARAMETER	SYMBOL	MIN	MAX	UNITS
DC Supply Voltage	V _{CC}	±2.5 or 5	±15 or 30	V
Operating Temperature	T _A	*	+70	°C

DC Electrical Characteristics (Target to the C unless otherwise specified)

DADAMETED	OVMDOL	CONDITIONS			LIMITS		LINUTO
PARAMETER	SYMBOL	JL GONDITIONS		MIN	TYP	MAX	UNITS
Input Offset Voltage	V _{IO}	V =1.4V, V _{CC} = 5V - 30V;	25°C	-	2	7	mV
input Onset voltage	VIO	$R_S = 0\Omega$, $V_{CC} = 0V$ to $V_{CC} = 1.7V$	70°C	-	-	9	IIIV
Input Offset Voltage Drift	ΔΥισ.ΔΤ	$V_{CC} = 30V; R_S =$	0Ω	-	7	-	μV/°C
			25°C	-	5	50	^
Input Offset Current	I _{IO}	I_{IO} $V_{CC} = 5V$	70°C	-	-	150	- nA
Input Offset Curion Drift	ΔΙ _{ΙΟ} /ΔΤ	$V_{CC} = 30V; R_S = 0\Omega$		-	10	-	pA/°C
Input Bas Current	I _{IB}	V _{CC} = 5V	25°C	-	45	250	nA
· ·	IIB	A CC — 2 A	70°C	-	40	500	11/5
Supply Current		R _L =∞,V _{CC} =5V, V _O	= 0V	-	0.5	1.2	mA
Supply Current	Supply Current I _{CC}		$R_L=\infty, V_{CC}=30V, V_O=0V$		1	2	IIIA
Common Mode Input	V	\/ - 30\/	25°C	0	-	V _{CC} -1.5	V
Voltage range	V _{ICR}	$V_{CC} = 30V$	70°C	0	-	V _{CC} -2	1 V
Differential Input Voltage range	V _{IDR}	All $V_{IN} \ge GND$ or V_{CC} - (if used)		-	-	V _{CC}	V



^{2.} $V_{IN} < -0.3V$. This input current exists when voltage is driven negative at any of the input leads



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specified)	70°C unless otherwise s	$(T_A = 0 \text{ to } 70^{\circ}\text{C})$	continued	eristics	Charact	C Flectrical	D(
sı	70°C unless otherwise s	$(T_A = 0 \text{ to } 70^{\circ}\text{C})$	continuea	eristics	Cnaract	C Electrical	D

PARAMETER	SYMBOL	CONDITIONS			LIMITS		UNITS
PARAMETER	STWIBOL			MIN	TYP	MAX	AND 13
Large-Signal Open-	A _{VOL}	V _{CC} =15V	25°C	25	100	-	V/mV
Loop Voltage Gain	AVOL	R _L ≥ 2KΩ	70°C	15	-	-	V/IIIV
Output High-Level	V _{OH}	V_{CC} =30V, R_L =2	ΚΩ	26	-		V
Voltage swing	V OH	V _{CC} =30V, R _L =10	ΙΚΩ	27	28	1	V
Output Low-Level Voltage swing	V _{OL}	V _{CC} =5V, R _L =10	ΚΩ	-	5	20	mV
Common-Mode Rejection Ratio	CMRR	V_{CC} =30V, R _S =10KΩ, T_A = 25°C		65	85	-	dB
Power Supply Rejection Ratio	PSSR	V _{CC} =30V, T _A = 25°C		65	100	-	dB
Crosstalk Attenuation	V _{O1} /V _{O2}	f =1KHz to 20KHz, V _{CC} =30V, T _A = 25°C		(5)	-120	-	dB
Output Short-Circuit current to GND	I _{SC}	$V_{CC} = 5V, V_{O} = 0V$ $T_{A} = 25^{\circ}C$		$O_{j_{j_{-}}}$	40	60	mA
Output Source	l	V_{IN} + = 1V, V_{IN} - =0V,	25°C	20	40	-	mA
Current	ISOURCE	$V_{CC} = 15V, V_{O} = 2V$	₩ 0°C	10	20	-	111/7
		V_{IN} + = 0V, V_{IN} - =1V,	25°C	10	20	-	mA
		$V_{CC} = 15V$, $V_O = 2V$	70°C	5	8	-	IIIA
Output Sink Current	VIN.		1V, .2V,	12	50	-	μA

Typical Characteristics

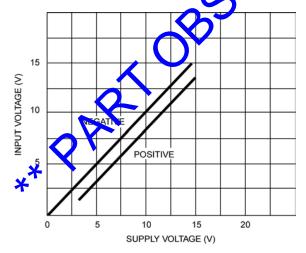


FIGURE 1. Input Voltage Range versus Supply Voltage

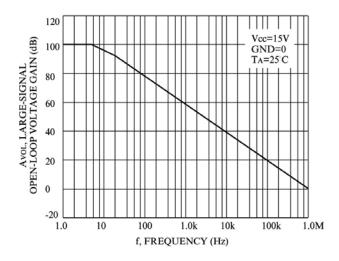


FIGURE 2. Open-Loop Frequency





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Typical Characteristics continued

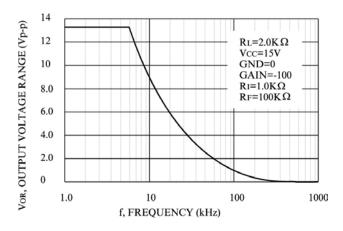


FIGURE 3. Large-Signal Frequency response

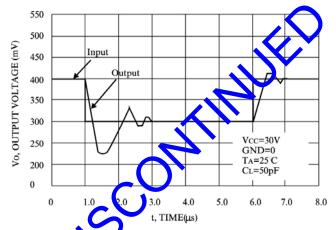


FIGURE Chall-Signal Voltage Follower Pulse Response (Non-inverting)

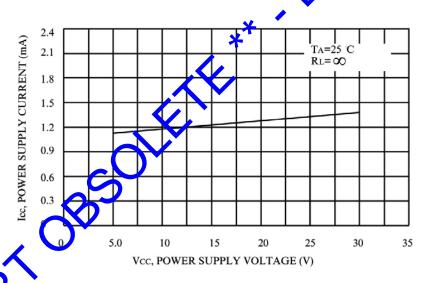


FIGURE 5. Power Supply Current versus Power Supply Voltage





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Typical Characteristics continued

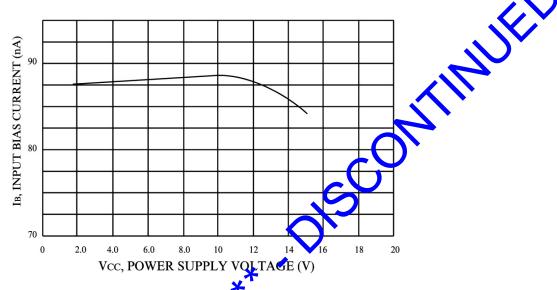
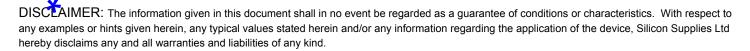


FIGURE 6. Low frequency Op-Amp with Offset adjust



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